

	Type	Hits	Search Text	DBs
1	IS&R	3	(310/327).CCLS.	FPRS; EPO; JPO; DERWENT; IBM TDB
2	BRS	732	sioc	USPAT
3	IS&R	7	(310/327).CCLS.	US-PGPUB
4	IS&R	225	(310/327).CCLS.	USPAT
5	BRS	0	"silicon oxide carbide" and high adj2 impedance same low adj2 impedance	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM TDB
6	BRS	27	sioc and carbide adj2 silicon adj1 oxide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM TDB
7	BRS	8	(sioc or (carbon adj2 silicon adj1 oxide)) and high adj2 impedance and low adj2 impedance	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM TDB
8	BRS	0	sioc and (acoustic adj1 (mirror or reflect\$4))	USPAT
9	BRS	0	"silicon oxide carbide" and acoustic adj2 (mirror or reflect\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM TDB
10	BRS	2	(sioc or (carbon adj2 silicon adj1 oxide)) and acoustic adj2 (mirror or reflect\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM TDB

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L9	694	(sio2 or "silicon oxide") same (sioc or "silicon oxide carbide")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWE NT; IBM_T DB	2007/07/1 1 09:17	
2	BRS	L10	202	19 and (mirror or reflect\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWE NT; IBM_T DB	2007/07/1 1 08:59	
3	BRS	L11	1	19 and (mirror or reflect\$4) same acoustic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWE NT; IBM_T DB	2007/07/1 1 08:59	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
4	BRS	L12	1	19 and (mirror or reflect\$4) same high adj2 impedance same low adj2 impedance	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2007/07/11 08:59	
5	BRS	L13	17	19 and piezoelectric	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2007/07/11 08:59	
6	BRS	L14	5	19 and acoustic	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2007/07/11 09:17	

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silicon oxide carbide

AND

AND

acoustic piezoelectric

OR

AND

AND

AND

Date of publication of application --- e.g. 19980401 - 19980405

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RESULT LIST

Approximately **269** results found in the Worldwide database for:
sioc or "silicon oxide carbide" in the title or abstract
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1 METHOD FOR FORMING METAL LINES IN A SEMICONDUCTOR DEVICE

Inventor: HAN JAE-WON (KR)

Applicant:

EC:

IPC: **H01L21/4763; H01L21/02**Publication info: **US2007148955** - 2007-06-28**2 SIOC:H COATED SUBSTRATES AND METHODS FOR THEIR PREPARATION**

Inventor: LOBODA MARK (US); SNOW STEVEN (US); (+2) Applicant: DOW CORNING (US)

EC: C23C16/40B; C23C16/455F; (+1)

IPC: **C23C16/30; H01L21/316; C23C16/30** (+1)Publication info: **EP1799877** - 2007-06-27**3 Method of manufacturing a semiconductor device**

Inventor: SASAKI YOICHI (JP); OHTO KOICHI (JP); (+3) Applicant: NEC ELECTRONICS CORP (JP)

EC: H01L21/768B; H01L21/768B2D

IPC: **H01L21/31; H01L23/522; H01L21/316** (+5)Publication info: **US2007117405** - 2007-05-24**4 Semiconductor device and manufacturing method thereof**

Inventor: OHMORI KAZUTOSHI (JP); TAMARU TSUYOSHI (JP); (+3)

Applicant:

EC:

IPC: **H01L21/4763; H01L21/02**Publication info: **US2007105369** - 2007-05-10**5 ACOUSTICAL SENSOR**

Inventor: MATSUBARA NAOTERU; NARUSE YOKO

Applicant: SANYO ELECTRIC CO

EC:

IPC: **H04R19/04; G01H11/06; G01N29/24** (+3)Publication info: **JP2007067893** - 2007-03-15**6 Method and structure for creating ultra low resistance damascene copper wiring**

Inventor: BURKE PETER A (US); LU HONGQIANG (US); (+1) Applicant: LSI LOGIC CORP (US)

EC:

IPC: **H01L23/48; H01L23/48**Publication info: **US7196420** - 2007-03-27**7 Method for producing hydrogenated silicon-oxycarbide films**

Inventor: LOBODA MARK J (US); HWANG BYUNG K (US) Applicant: DOW CORNING

EC: C23C16/30

IPC: **H01L21/44; C23C16/30; H01L21/31** (+2)Publication info: **US2006148252** - 2006-07-06**8 PROCESS FOR PREPARATION OF SiOC-LINKED, LINEAR POLYDIMETHYLSILOXANE-POLYOXYALKYLENE BLOCK COPOLYMERS**

Inventor: KNOTT WILFRIED (DE); LANDERS RUEDIGER (DE); (+1) Applicant: GOLDSCHMIDT GMBH (DE)

EC:

IPC: **C08G77/06; C08G77/04; C08L83/04** (+2)Publication info: **US2007049717** - 2007-03-01**9 METHOD OF MANUFACTURING SEMICONDUCTOR**

Inventor: KISHIGAMI DAIZO

Applicant: TOSHIBA CORP

EC:

IPC: **H01L21/306; H01L21/265; H01L21/336** (+3)Publication info: **JP2007042885** - 2007-02-15

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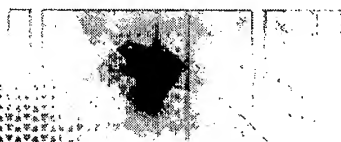
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- | Title | Pub. Date | Int. Class | Applicant |
|--|------------|-------------|------------------------------|
| 1. (WO 2007/053407) THICK CRACK-FREE SILICA FILM BY COLLOIDAL SILICA INCORPORATION | 10.05.2007 | C08L 83/04 | HONEYWELL INTERNATIONAL INC. |
| <p>The invention relates to low temperature curable spin-on glass materials which are useful for electronic applications, such as optical devices, in particular for flat panel displays. A substantially crack-free silicon polymer film is produced by (a) preparing a composition comprising at least one silicon containing pre-polymer, colloidal silica, an optional catalyst, and optional water; (b) coating a substrate with the composition to form a film on the substrate, (c) crosslinking the composition by heating to produce a substantially crack-free silicon polymer film, having a thickness of from about 700 Å to about 20,000 Å, and a transparency to light in the range of about 400 nm to about 800 nm of about 90% or more.</p> | | | |
| 2. (WO 2006/017450) LOW TEMPERATURE CURABLE MATERIALS FOR OPTICAL APPLICATIONS | 16.02.2006 | H01L 21/312 | HONEYWELL INTERNATIONAL INC. |
| <p>The invention relates to low temperature curable spin-on glass materials which are useful for electronic applications, such as optical devices. A substantially crack-free and substantially void-free silicon polymer film is produced by (a) preparing a composition comprising at least one silicon containing pre-polymer, a catalyst, and optionally water; (b) coating a substrate with the composition to form a film on the substrate, (c) crosslinking the composition by heating to produce a substantially crack-free and substantially void-free silicon polymer film, having a transparency to light in the range of about 400 nm to about 800 nm of about 95 % or more.</p> | | | |
| 3. (WO 2005/114707) MATERIALS SUITABLE FOR SHALLOW TRENCH ISOLATION | 01.12.2005 | H01L 21/762 | HONEYWELL INTERNATIONAL INC. |
| <p>The invention relates to semiconductor device fabrication and more specifically to a method and material for forming of shallow trench isolation structures in integrated circuits. A silica dielectric film is formed by preparing a composition comprising a silicon containing pre-polymer, optionally water, and optionally a metal-ion-free catalyst selected from the group consisting of onium compounds and nucleophiles. The substrate is then coated with the composition to form a film. The film is then crosslinked to produce a gelled film. The gelled film is then heated at a temperature of from about 750 °C to about 1000 °C for a duration effective to remove substantially all organic moieties and to produce a substantially crack-free silic...</p> | | | |
| 4. (WO 2004/114386) METHODS AND SYSTEM FOR PROCESSING A MICROELECTRONIC TOPOGRAPHY | 29.12.2004 | H01L 21/288 | BLUE29 CORPORATION |
| <p>Methods and systems are provided which are adapted to process a microelectronic topography, particularly in association with an electroless deposition process. In general, methods are provide which include loading a topography into a chamber and supplying fluids to an enclosed area about the topography. In particular, a method is provided for forming a hydrated metal oxide layer. In addition, a method is provided for selectively depositing a dielectric layer and a metal layer upon a topography. A topography having a single layer with at least four elements lining a lower surface and sidewalls of a metal feature is also provided. A process chamber which includes a gate configured to either seal or provide an air passage to the chamber and a ...</p> | | | |
| 5. (WO 2004/064983) TREATMENT OF EFFLUENT FROM A SUBSTRATE PROCESSING CHAMBER | 05.08.2004 | B01D 53/32 | APPLIED MATERIALS, INC. |
| <p>A substrate processing apparatus has a process chamber and an effluent treatment reactor (50). The effluents treatment reactor has an effluent inlet (23) to receive effluent from the exhaust conduit of the process chamber, a plasma cell (35) having one or more electrodes (14), (16) electrically connected to a voltage source adapted to electrically bias the electrodes to couple energy to effluent received in the plasma cell, a scrubbing cell (30) coaxially exterior to the plasma</p> | | | |



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GROWTH OF SILICON SINGLE CRYSTALS,
SIMILAR UNIDIRECTIONAL GROWTH
METHODS AND SIMILAR
SEMICONDUCTOR MATERIALS, AND
OTHER APPLICATIONS REQUIRING
REDUCED CHEMICAL REACTIVITY OF
FUSED SILICA
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MATERIAL FOR A LITHIUM ION BATTERY
7. [2160428](#) METHOD FOR THE PREPARATION OF 77%